

3w 5w 8w 808nm Single Emitter Bare Laser Chip

Main application is medical, laser lighting, free space optical communication.

The conversion efficiency of our chip can reach 60%, and lifetime can be more than 10000 hours. In addition, the chip also adopts new epitaxial structure design and material epitaxy, advanced non-pump window design and preparation technology, and wet and dry etching combined with self-aligned process technology to control the consistency of the strip width, especially to increase the manufacturing yield, also to reduce laser chip cost.

At the same time, the adoption of new technology greatly improves the high temperature resistance characteristics, so that it can work continuously at an ambient temperature of 60 °C or higher.



Data Sheet

Item No:LC808SE3,LC808SE5,LC808SE8

Item Name:3w 5w 8w 808nm Bare Laser Chip

Operation

Center wavelength	808nm	808nm	808nm
Output power	3W	5W	8W
Operation mode	cw	cw	cw

Geometrical

Emitter width	20100um	200um	200um
Cavity length	2000um	2000um	4000um
Emitter Pitch	500um	500um	600um
Thickness	125um	125um	125um

Electro Optical Data

Threshold current	0.4A	0.8A	1.25A
Operating current	2.8A	4.8A	8.5A
Operating voltage	1.75v		
Slope efficiency	1.22W/A	1.25W/A	1.2W/A
Conversion efficiency	61%	60%	55%
Slow axis divergence	8	8	10
Fast axis divergence	36		
Spectral width	3nm		
Polarization	TE		

PIV Chart for 3W 808nm Laser Chip:

